

SP-C300 Series Silicon Technology :ARC/SOG/SOD/Slurry

<b>产品名称</b> <b>Product Name:</b>		<b>SP-C3650 紫外光固化防反射涂层</b> <b>SP-C3650N UV Curing Anti-reflective Coatings for OLED-Electronics &amp; IC</b>	
<b>Technique Feature:</b>			
<b>Applications</b>		C3650 UV Curing Anti-reflective Coatings is a Spin-On-Material, applied to a clean silicon wafer by spin-on-coating just like photoresist for: <ol style="list-style-type: none"> <li>1. Dielectric Barrier Layer for Liftoff technique by SOG</li> <li>2.interconnected planarization of IC-semi-conductors</li> <li>3. device-circuit isolation.</li> <li>4. thick dielectric/spin-on or CVD glass.</li> <li>5.Anti-reflective Coatings for Electronics, IC, OLED, DSSC</li> </ol>	
<b>Technical Description</b>		<ol style="list-style-type: none"> <li>1.C3650 UV Curing Anti-reflective Coatings are used with the Silicon lithography process to improve the photoresist profile and reduce the line width variation caused by scattering and reflecting light.</li> <li>2.C3650 UV Curing Anti-reflective Coatings, using a Spin-On-Glass Material(SOG) method, is a solution of SiO<sub>2</sub>, and organic solvent. It can be SiO<sub>2</sub> blended in Anhydrous alcohol solvent, which is specified C3652, while it is mixed with dopants (either boron or phosphorous) that is suspended in a solvent solution, which is specified C3652,which can be a dielectric layer in our category.</li> <li>3. C3650 ARC is a non-photo-imageable type coating material, and Apply C3560 SOG using same technique as negative photoresist of i line, without imaging developed</li> <li>4. the ARC-SOG is typically immiscible in alcohol solvent.</li> <li>5. the pH, which is typically around 10, is maintained so as to keep the silica particles negatively charged to avoid the formation of a large gel network..</li> <li>6.Excellent adhesion to ITO, Silicon, metals,PET,etc.</li> <li>7.Good resistant to moisture, acid, alkali, solvent</li> <li>8.suitable for spin,roll, pray coating types</li> <li>9.good resistant to high-temperature@500°C-800°C/20mins</li> </ol>	
<b>Technical Process:</b>			
<b>Pre-treatment of wafer surface</b>		Chemical and physical(scrubbing etc) treatment	
<b>Spin-on Deposition/Glass</b>		While viscosity:2.70±0.20mPa.s@25°C, SOG4000rpm,forming film less than 1um, 3000rpm,forming a film < 1.7um; 2000rpm,forming a film < 2.5-2.6um。	
<b>Key Technical Points to note</b>	<b>Age(gelation)</b>	@50-150°C/( gelation):10-25mins	
	<b>Dry</b>	@>100°C	
	<b>Anneal</b>	@>300°C	
<b>SOG Applying Procedure</b>		Spin-on-glass <ol style="list-style-type: none"> <li>1. Bring SOG up to room temperature by leaving it in the lab for 30 minutes.</li> <li>2.Heating (heat 1 minute at 80°C)</li> </ol>	

	<p>3. Apply SOG using same technique as photoresist (spin at 3000-4000rpm) depending on the thickness of the film required: So Spin SOG</p> <p>4. Bake at 80°C for 1 minute</p> <p>5. Bake at 150°C for 1 minute</p> <p>6. UV Curing: Exposure: i line@365nm wavelength</p> <p>7. Bake at 250°C for 1 minute</p> <p>8. Cure in furnace at 425°C for 1 hour</p> <p>Note that the lifetime of the SOG is dramatically reduced when the product is heated to room temperature.</p> <p>The remaining SOG must therefore be discarded after use.</p>
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<b>产品名称</b> Product Name:	<b>SP-C3652 用于 OLED-Electronics &amp; IC 光成像 SOG 防反射涂层</b> <b>SP-C3652 Photo-Imageable Anti-reflective SOG Coatings for OLED-Electronics &amp; IC</b>
<b>Technique Feature:</b>	
<b>Applications</b>	<p>C3652 UV Curing Anti-reflective Coatings is a Spin-On-Material, applied to a clean silicon wafer by spin-on-coating just like photoresist for:</p> <ol style="list-style-type: none"> <li>1. Dielectric Barrier Layer for Liftoff technique by SOG</li> <li>2. interconnected planarization of IC-semi-conductors</li> <li>3. device-circuit isolation.</li> <li>4. thick dielectric/spin-on or CVD glass.</li> <li>5. Anti-reflective Coatings for Electronics, IC, OLED, DSSC</li> </ol>
<b>Technical Description</b>	<ol style="list-style-type: none"> <li>1. C3652 UV Curing Anti-reflective Coatings are used with the Silicon lithography process to improve the photoresist profile and reduce the line width variation caused by scattering and reflecting light.</li> <li>2. C3652 UV Curing Anti-reflective Coatings, using a Spin-On-Glass Material(SOG) method, is a solution of SiO<sub>2</sub> and organic polysiloxane, solvent. It can be SiO<sub>2</sub> blended in Anhydrous alcohol solvent, which is mixed with dopants (either boron or phosphorous) that is suspended in a solvent solution, which is specified C3652, which can be a dielectric layer in our category.</li> <li>3. C3652 ARC is a non-photo-imageable type coating material, and Apply C3652 SOG using same technique as negative photoresist of i line, without imaging developed</li> <li>4. the ARC-SOG is typically immiscible in alcohol solvent.</li> <li>5. the pH, which is typically around 10, is maintained so as to keep the silica particles negatively charged to avoid the formation of a large gel network..</li> <li>6. Excellent adhesion to ITO, Silicon, metals, PET, etc.</li> <li>7. Good resistant to moisture, acid, alkali, solvent</li> <li>8. suitable for spin, roll, pray coating types</li> <li>9. good resistant to high-temperature@500°C-800°C/20mins</li> </ol>
<b>Technical Process:</b>	
<b>Pre-treatment of wafer surface</b>	Chemical and physical (scrubbing etc) treatment
<b>Spin-on Deposition/Glass</b>	While viscosity: $2.70 \pm 0.20 \text{ mPa.s}$ @ 25°C, SOG 4000rpm, forming film less than 1.2um,

		3000rpm,forming a film <1.7um; 2000rpm,forming a film < 2.5-2.6um。
Key Technical Points to note	Age(gelation)	@50-150°C/( gelation):10-25mins
	Dry	@>100°C
	Anneal	@>300°C
SOG Applying Procedure		<p>Spin-on-glass</p> <ol style="list-style-type: none"> <li>1. Bring SOG up to room temperature by leaving it in the lab for 30 minutes.</li> <li>2.Heating (heat 1 minute at 80°C)</li> <li>3. Apply SOG using same technique as photoresist (spin at 3000-4000rpm) depending on the thickness of the film required: So Sin SOG</li> <li>4. Bake at 80°C for 1 minute</li> <li>5. Bake at 150°C for 1 minute</li> <li>6. Exposure: i line@365nm wavelength</li> <li>7. Developing: immersing the coated and exposed film-board into the alkaline developer</li> <li>8. Bake at 250°C for 1 minute</li> <li>9. Cure in furnace at 425°C for 1 hour</li> </ol> <p>Note that the lifetime of the SOG is dramatically reduced when the product is heated to room temperature. The remaining SOG must therefore be discarded after use.</p>

产品名称 Product Name:	<b>SP-C3112 用于 OLED-LED-Electronics &amp; IC UV 固化 SOG 涂层</b> <b>SP-C3112 UV Curing SOG for OLED-LED-Electronics &amp; IC</b>
<b>Technique Feature:</b>	
Applications	<p>C3112 UV Curing is a Spin-On-Material, applied to a clean silicon wafer by spin-on-coating just like photoresist for:</p> <ol style="list-style-type: none"> <li>1. Dielectric Barrier Layer for Liftoff technique by SOG</li> <li>2. interconnected planarization of IC-semi-conductors</li> <li>3. device-circuit isolation.</li> <li>4. thick dielectric/spin-on or CVD glass.</li> <li>5.Anti-reflective Coatings for Electronics, IC, OLED, DSSC</li> </ol>
Technical Description	<ol style="list-style-type: none"> <li>1.C3112 UV Curing series are used with the Silicon lithography process to improve the photoresist profile and reduce the line width variation caused by scattering and reflecting light.</li> <li>2.C3112 UV Curing, using a Spin-On-Glass Material(SOG) method, is a solution of SiO<sub>2</sub> and organic solvent. It can be SiO<sub>2</sub> blended in Anhydrous alcohol solvent, which is specified C3112, while it is mixed with dopants (either boron or phosphorous) that is suspended in a solvent solution, which is specified C3122 in our category.</li> <li>3. C3112 ARC is a non-photo-imageable but UV curing type coating material, and Apply C3112 SOG using same technique as negative photoresist, without imaging developed</li> <li>4. the SOG is typically immiscible in alcohol solvent.</li> <li>5. the pH, which is typically around 10, is maintained so as to keep the silica particles negatively charged to avoid the formation of a large gel network..</li> <li>6.Excellent adhesion to ITO, Silicon, metals, PET, etc.</li> </ol>

		7.Good resistant to moisture, acid, alkali, solvent 8.suitable for spin coating types 9.good resistant to high-temperature@500°C-800°C/20mins
<b>Technical Process:</b>		
Pre-treatment of wafer surface		Chemical and physical(scrubbing etc) treatment
Spin-on Deposition/Glass		While viscosity:2.70±0.20mPa.s@25°C, SOG4000rpm,forming film less than 1.2um, 3000rpm,forming a film < 1.7um; 2000rpm,forming a film < 2.5-2.6um。
Key Technical Points to note	Age(gelation)	@50-150°C/( gelation):10-25mins
	Dry	@>100°C
	Anneal	@>300°C
SOG Applying Procedure		Spin-on-glass 1. Bring SOG up to room temperature by leaving it in the lab for 30 minutes. 2.Heating (heat 1 minute at 80°C) 3. Apply SOG using same technique as photoresist (spin at 3000-4000rpm) depending on the thickness of the film required: So Sin SOG 4. Bake at 80°C for 1 minute 5. Bake at 150°C for 1 minute 6. UV Curing: Exposure: i line@365nm wavelength 7. Bake at 250°C for 1 minute 8. Cure in furnace at 425°C for 1 hour Note that the lifetime of the SOG is dramatically reduced when the product is heated to room temperature. The remaining SOG must t herefore be discarded after use.

产品名称 Product Name:	<b>SP-C31910 半导体/集成电路 CMP 用研磨剂涂层</b> <b>SP-C31910 Colloid Slurry for Chemical Mechanical Planarization(CMP)</b>
<b>Technique Feature:</b>	
Features	1. Colloid slurries of abrasive type: SiO <sub>2</sub> . 2. Alkaline slurry containing colloid silica(a suspension of abrasive SiO <sub>2</sub> particles). 3. KOH and NH <sub>4</sub> OH are common matrix solutions for the suspension. 4. Colloidal slurry is typically immiscible in alcohol solvent. 5. the pH, which is typically around 10, is maintained so as to keep the silica particles negatively charged to avoid the formation of a large gel network..
Applications:	1. interconnected planarization. 2.device isolation. 3.thick dielectric/spin-on or CVD glass.
<b>Chemical Description:</b>	

<b>Nano-Slurry for Wafer Polish of CMP/ SP-C31910 Colloidal Silica Slurry</b>	
Abrasive	Colloidal Silica Slurry
pH	10.4
%Solid Content	30
Average Particle Size/APS(nm)	20
Density	1.06
Viscosity(25°C)	2.6±0.20mPa.s
Trace Metals at POU(ppm)	
Na	140
As	4
Ca	90
	6
<b>Suggested Technical Process:</b>	
Pre-treatment of wafer surface	Chemical and physical(scrubbing etc) treatment
Spin-on Deposition/Glass	While viscosity:2.70±0.20mPa.s@25°C, SOG4000rpm,forming 1 film of 1.2um, 3000rpm,forming a film of 1.7um; 2000rpm,forming a film of 2.5-2.6um
Age(gelation)	@50-150°C/( gelation):10-25mins
Dry	@>100°C
Anneal	@>300°C
Optional Hydrophobic treatment	Optional Hydrophobic treatment

公司供应专本感光胶用稀释剂、专用显影液、专用脱膜剂。

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